

**UNIVERSITY OF SWAZILAND**  
**SUPPLEMENTARY EXAMINATION, JULY 2009**

**FACULTY OF SCIENCE**

**DEPARTMENT OF ELECTRICAL AND ELECTRONIC  
ENGINEERING**

**TITLE OF PAPER: ANALOGUE ELECTRONICS IV**

**COURSE CODE: E512**

**TIME ALLOWED: THREE HOURS**

**INSTRUCTIONS:**

- 1. There are five questions in this paper. Answer any FOUR questions.  
Each question carries 25 marks.**
- 2. Unless otherwise stated,  $V_{BE(ON)} = 0.7 \text{ V}$  and  $V_T = 0.025 \text{ V}$ .**
- 3. If you think not enough data has been given in any question you may  
assume any reasonable values.**
- 4. A sheet containing some useful equations is attached at the end of this  
examination paper.**
- 5. Smith Charts which may be used to solve some problems are attached.**

**THIS PAPER SHOULD NOT BE OPENED UNTIL PERMISSION  
HAS BEEN GIVEN BY THE INVIGILATOR**

**THIS PAPER CONTAINS EIGHT (8) PAGES INCLUDING THIS PAGE**

**QUESTION ONE (25 marks)**

- (a) At an ambient temperature  $T_A = 25^\circ\text{C}$ , a BJT is specified to have a maximum power dissipation  $P_{D\text{max}}$  of 20 W and a maximum junction temperature  $T_{J\text{max}}$  of  $150^\circ\text{C}$ . Find the following:
- The thermal resistance  $\theta_{JA}$  of the BJT. (3 marks)
  - The maximum power that it can safely dissipate at an ambient temperature of  $50^\circ\text{C}$ . (3 marks)
  - The junction temperature when the device is dissipating 10 W at an ambient temperature of  $25^\circ\text{C}$ . (3 marks)
- (b) Consider the class AB output stage using a  $V_{BE}$  multiplier as shown in Fig Q.1b. In this circuit  $V_{CC} = 15\text{ V}$ ,  $R_L = 100\ \Omega$ , and the output  $V_o$  is sinusoidal with a maximum amplitude of 10 V. Let  $Q_N$  and  $Q_P$  be matched with  $I_S = 10^{-13}\text{ A}$  and  $\beta = 50$ .
- Suggest with justification a suitable value for the bias current  $I_{\text{bias}}$  for the circuit to work properly. (4 marks)
  - For a quiescent current of  $I_Q = 2\text{ mA}$  in the output transistors, what bias voltage should the  $V_{BE}$  multiplier provide? (5 marks)
  - If the  $V_{BE}$  multiplier transistor  $Q_1$  has  $I_S = 10^{-14}\text{ A}$  and a large  $\beta$ , complete the design by specifying the values of  $R_1$  and  $R_2$  that would result in the bias voltage you worked out in (ii). (7 marks)

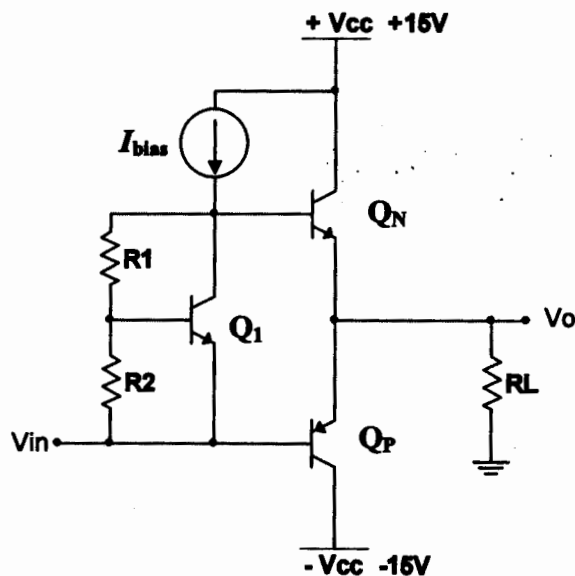
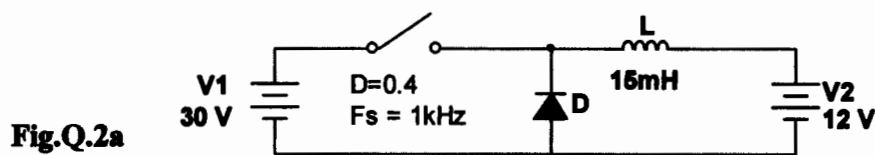


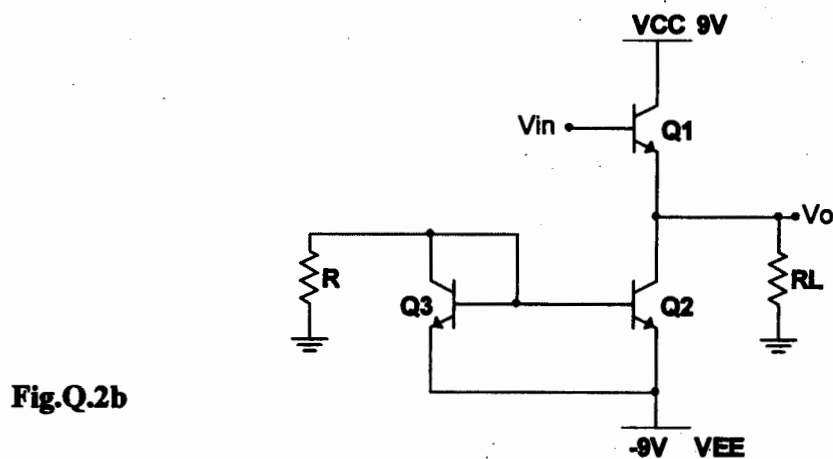
Fig.Q.1b

**QUESTION TWO (25 marks)**

- (a) A 12V battery  $V_2$  is being charged using a 30 V source  $V_1$  through an inductor in a switching mode as shown in Fig.Q.2a. The switch is operating at 1 kHz with a duty cycle of 0.4. The inductor is designed to make the charging current smooth with a tolerable ripple. What value of inductor will limit the peak-to-peak current to 100 mA? (5 marks)



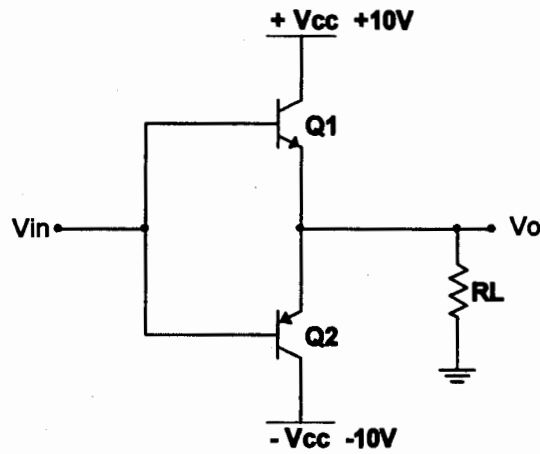
- (b) For the emitter follower power amplifier stage shown in Fig.Q.2b. with  $\pm 9\text{ V}$  supplies and BJTs with high  $\beta$ , find a value of  $R$  which would give a design capable of  $\pm 7\text{ V}$  outputs with a  $1\text{-k}\Omega$  load  $R_L$ . (5 marks)



- (c) For the class B complementary stage shown in Fig.Q.2c with  $\pm 10\text{ V}$  supplies and a  $100\text{-}\Omega$  load  $R_L$ , assume that  $V_{CEsat} = 0.3\text{ V}$  and  $V_{BE} = 0.7\text{ V}$ . Calculate the following:
- The maximum sinewave output power available. (5 marks)
  - The maximum input signal. (2 marks)

**Question 2(c) Continued ...**

- (iii) The average power dissipation of each BJT. (5 marks)
- (iv) The maximum efficiency of the stage. (3 marks)



**Fig.Q.2c**

**QUESTION THREE (25 marks)**

The amplifier whose schematic is shown in Fig.Q.3 is dc coupled throughout and is biased using the three current sources shown. The n-type transistors are matched with  $\beta_N = 100$ , and the p-type transistors are also matched with  $\beta_P = 75$ . By performing step-by-step dc analysis of each stage of the amplifier, determine the output voltage  $V_o$  appearing across a load resistance  $R_L$  of  $1\text{ k}\Omega$ . Note that dc coupled stages interact and base currents are not negligible for all the transistors.

(25 marks)

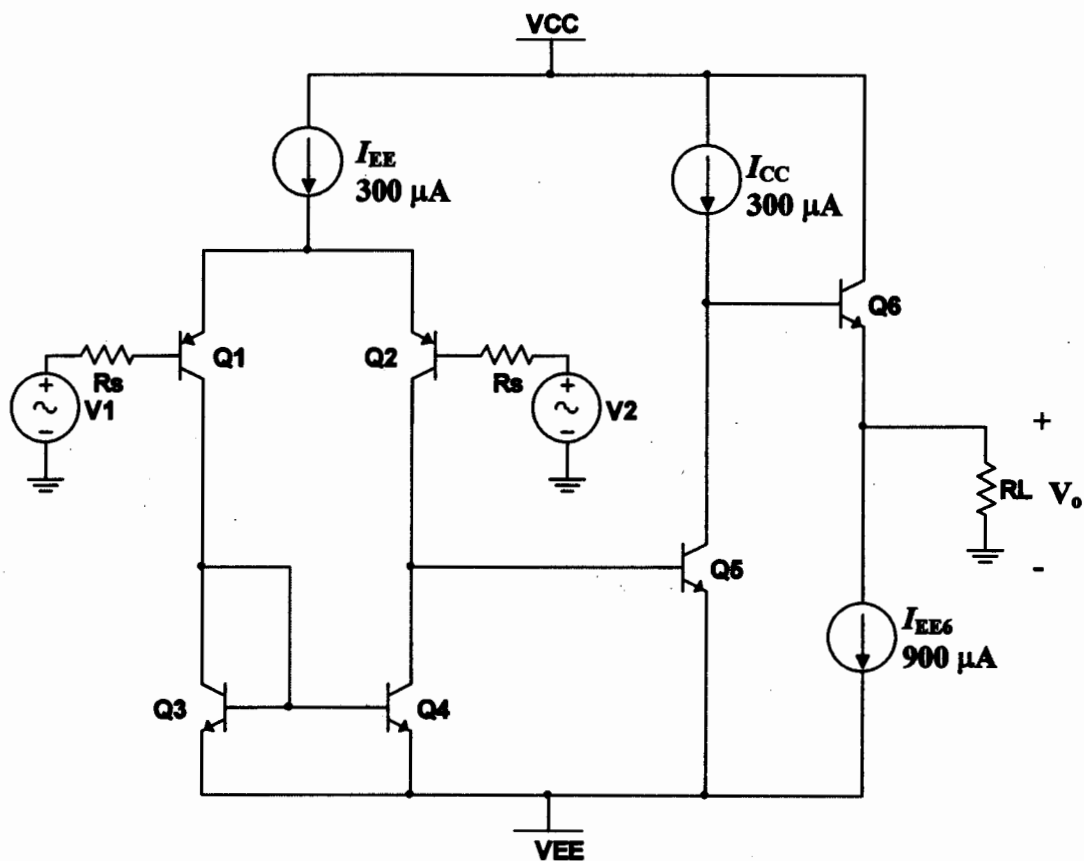


Fig.Q.3

**QUESTION FOUR** (25 marks)

(a) A signal source has a signal-to-noise ratio of 20 dB and produces signal power of  $50\mu\text{W}$  to a matched load. The signal from the source is amplified by a matched amplifier whose gain is 35 dB. The amplifier itself produces noise of 200 nW referred to its input. Calculate:

(i) The noise power in the source. (4 marks)

(ii) The noise figure of the amplifier. (6 marks)

(b) Determine and sketch the components of an L-section matching network for matching a  $75\ \Omega$  source to a load of  $300\ \Omega$  at a frequency of 100 MHz.

(15 marks)

**QUESTION FIVE (25 marks)**

A transistor 2N5179 at  $V_{CE} = 6.0$  V,  $I_C = 1.5$  A has the following  $y$ -parameters at 300 MHz:

$$y_{11} = 4.8 + j9.6 \text{ mS}$$

$$y_{12} = -0.09 - j1.15 \text{ mS}$$

$$y_{21} = 36.5 - j26.8 \text{ mS}$$

$$y_{22} = 0.42 + j2.65 \text{ mS}$$

- (a) Examine the stability of the device at this bias point and frequency. Is the device usable? Explain your answer. (8 marks)
- (b) Up to what power amplification would you expect the device to give under ideal conditions? (5 marks)
- (c) The device is driven from from a source of  $70 \Omega$  and feeds into a  $100 \Omega$  load.  
Draw the  $y$ -parameter equivalent circuit and calculate the voltage gain of the circuit.

(12 marks)